

P-Ch 100V Fast Switching MOSFETs

Features:

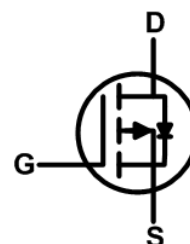
- ★ Advanced Trench MOS Technology
- ★ 100% EAS Guaranteed
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Green Device Available



Applications

- ★ High Frequency Switching and Synchronous Rectification.
- ★ DC/DC Converter

PRPAK3x3 Pin Configuration



Product Summary

BVDSS	RDS(on)	ID
-100V	95mΩ	-14A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-14	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-8.7	A
I_{DM}	Pulsed Drain Current ²	-56	A
EAS	Single Pulse Avalanche Energy ³	157.2	mJ
I_{AS}	Avalanche Current	18.9	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	31	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	65	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-10A	---	---	95	mΩ
		V _{GS} =-4.5V, I _D =-8A	---	---	110	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.7	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-100V, V _{GS} =0V, T _J =25°C	---	---	-50	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-10A	---	24	---	S
Q _g	Total Gate Charge	V _{DS} =-50V, V _{GS} =-10V, I _D =-10A	---	44.5	---	nC
Q _{gs}	Gate-Source Charge		---	9.13	---	
Q _{gd}	Gate-Drain Charge		---	5.93	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-50V, V _{GS} =-10V, R _G =3.3Ω, I _D =-10A	---	12	---	ns
T _r	Rise Time		---	27.4	---	
T _{d(off)}	Turn-Off Delay Time		---	79	---	
T _f	Fall Time		---	53.6	---	
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	---	3029	---	pF
C _{oss}	Output Capacitance		---	129	---	
C _{rss}	Reverse Transfer Capacitance		---	76	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	-14	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-8A, di/dt=-100A/μs, T _J =25°C	---	38.7	---	nS
Q _{rr}	Reverse Recovery Charge		---	22.4	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%

3.The EAS data shows Max. rating. The test condition is V_{DD}=-25V, V_{GS}=-10V, L=0.88mH, I_{AS}=-18.9A

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

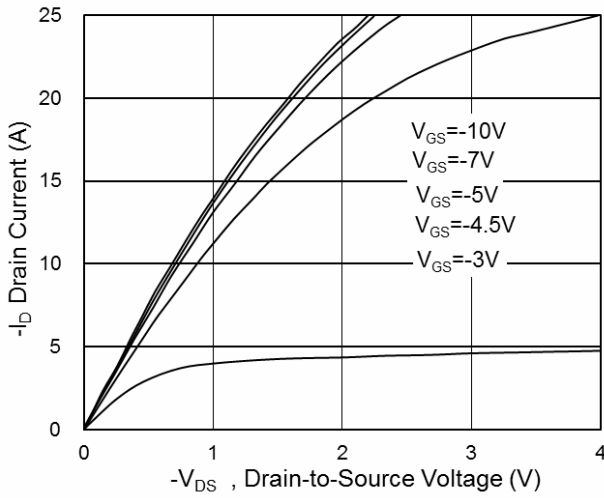


Fig.1 Typical Output Characteristics

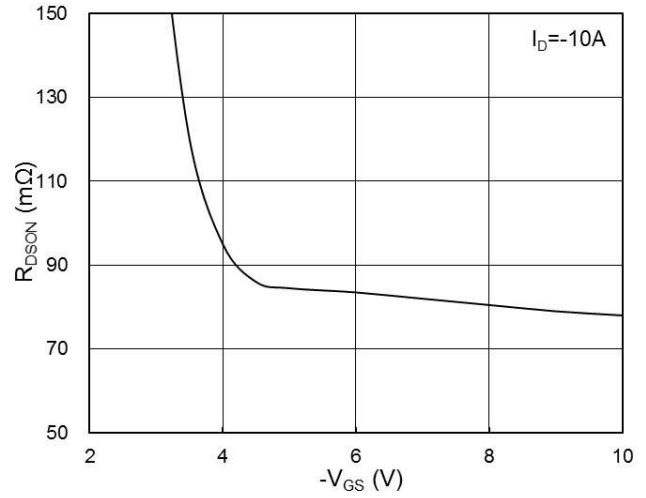


Fig.2 On-Resistance vs. G-S Voltage

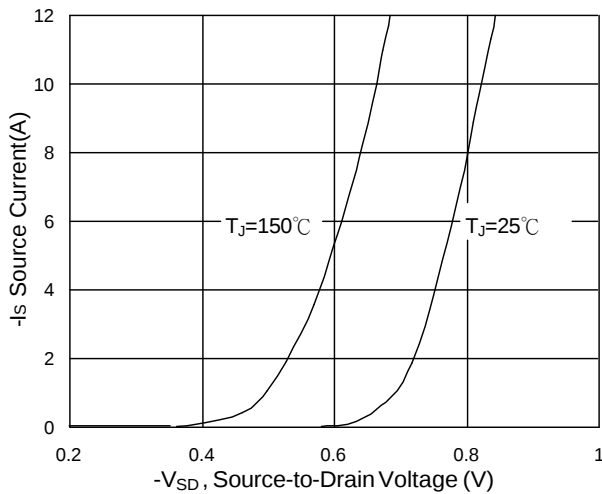


Fig.3 Typical S-D Diode Forward Voltage

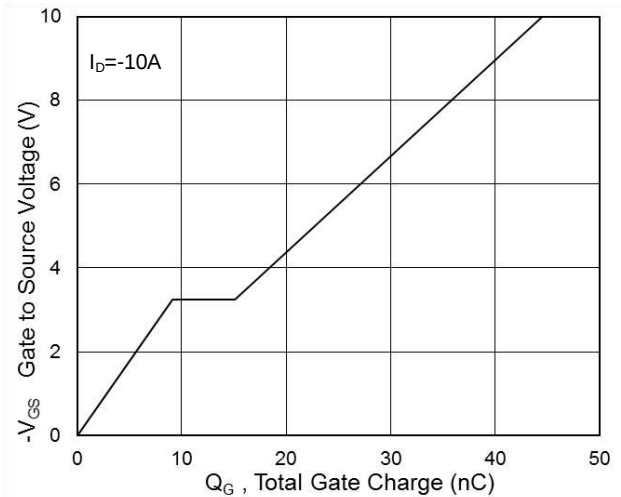


Fig.4 Gate-Charge Characteristics

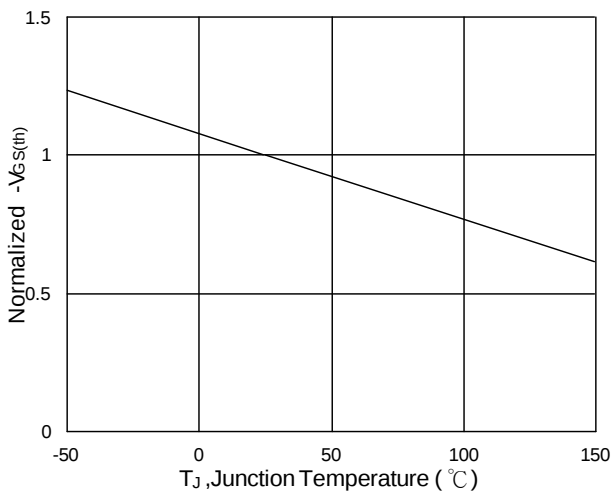


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

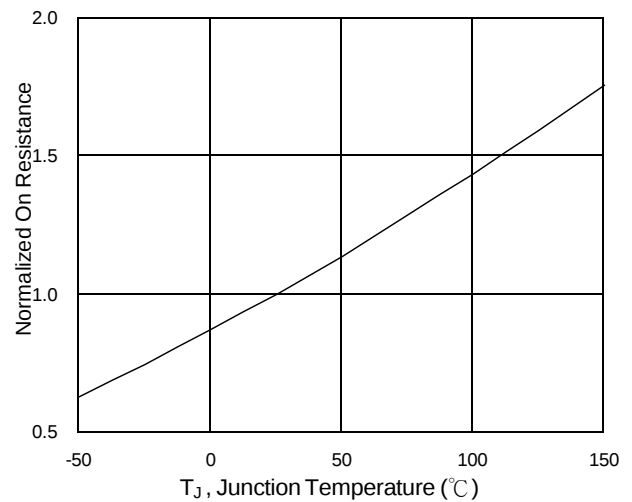


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

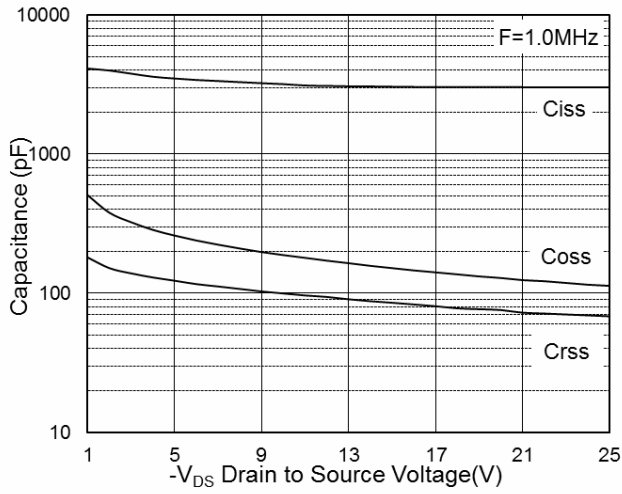


Fig.7 Capacitance

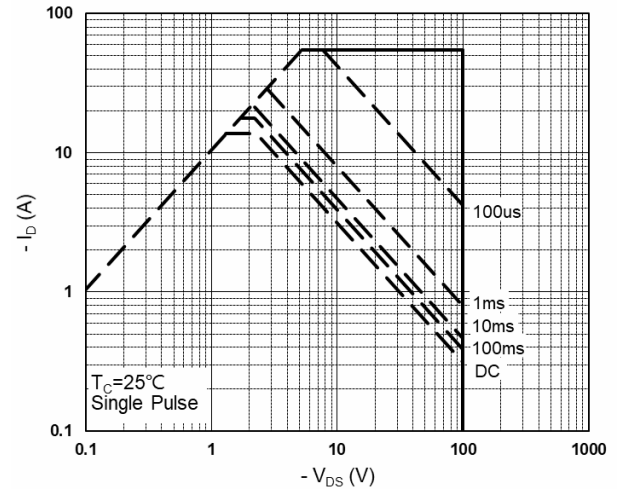


Fig.8 Safe Operating Area

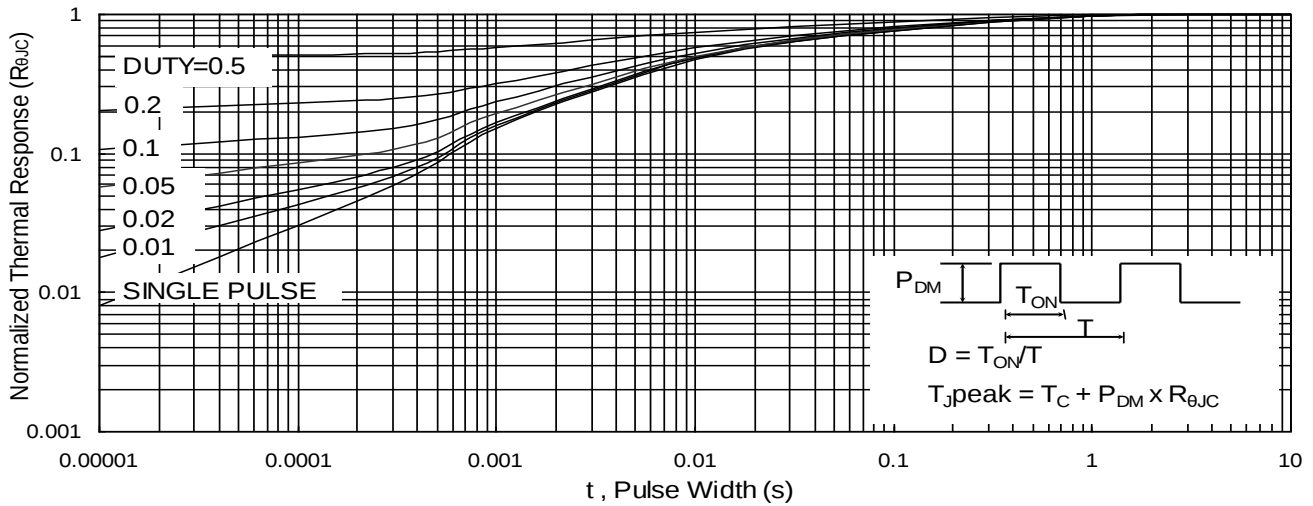


Fig.9 Normalized Maximum Transient Thermal Impedance

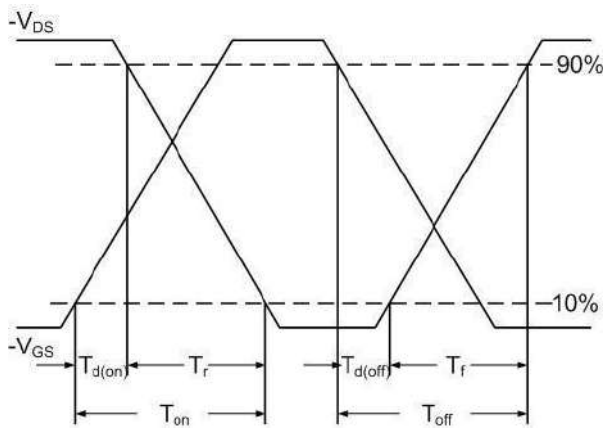


Fig.10 Switching Time Waveform

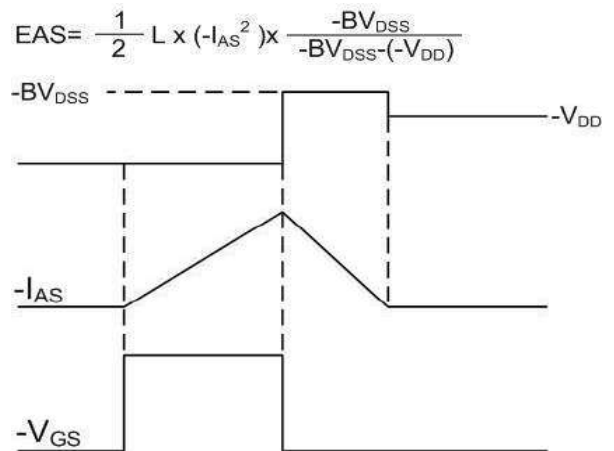


Fig.11 Unclamped Inductive Waveform